Notice of References Cited Application/Control No. 10/696,079 Examiner Anh D. Mai Applicant(s)/Patent Under Reexamination LIM ET AL. Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-4,808,259	02-1989	Jillie et al.	438/593
	В	US-5,086,017	02-1992	Lu, Chih-Yuan	438/586
	O	US-5,190,887	03-1993	Tang et al.	438/264
	D	US-5,631,178	05-1997	Vogel et al.	438/200
	E	US-5,637,151	06-1997	Schulz, Peter	134/2
	F	US-6,093,659 A	07-2000	Grider et al.	438/758
	G	US-6,436,771 B1	08-2002	Jang et al.	438/275
	Н	US-6,597,046 B1	07-2003	Chau et al.	257/411
	ı	US-6,787,421 B2	09-2004	Gilmer et al.	438/275
	J	US-2003/0113959 A1	06-2003	Min et al.	438/151
	к	US-2003/0157772 A1	08-2003	Wieczorek et al.	438/287
	٦	US-2004/0023506 A1	02-2004	Pradeep et al.	438/710
	М	US-2004/0102010 A1	05-2004	Khamankar et al.	438/287

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N				,	
	0					
	Р					
	α					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)					
	U	H. Lim et al., The Effects of STI Process Parameters on the integrity of Dual Gate Oxides. IEEE 2001, pp. 48-51.					
	V						
	w						
	х						

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.